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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 South Federal Way, Boise, ID 83716-9632 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **SANDHU, Gurtej, S.** [GB/US]; 2964 East Parkriver Drive, Boise, ID 83706 (US). **YIN, Zhiping** [US/US]; 1462 East Regatta Street, Boise, ID 83706 (US). **LI, Weimin** [US/CN]; 18 Qington Road #43-502, Pudong New Area, Shanghai 201203 (CN).

(74) Agents: **STEFFEY, Charles, E.** et al.; P.O. Box 2938, Minneapolis, MN 55402 (US).

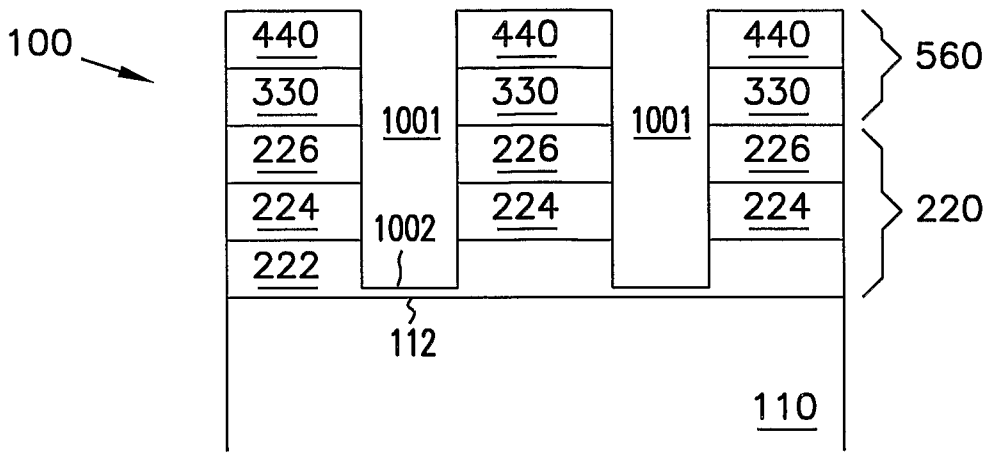
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(54) Title: MASKING STRUCTURE INCLUDING AN AMORPHOUS CARBON LAYER



(57) Abstract: A masking structure having multiple layers is formed. The masking structure includes an amorphous carbon layer and a cap layer formed over the amorphous carbon layer. The amorphous carbon layer includes transparent amorphous carbon. The cap layer includes non-oxide materials. The masking structure may be used as a mask in an etching process during fabrication of semiconductor devices.

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